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Attorney Docket No.: 0553-0152.02 IN THE UNITED STATES PATENT AND TRADEMARK OFFICE pplication of: I hereby certify that this correspondence is being) deposited with the United States Postal Service as first Shunpei YAMAZAKI et al. class mail in an envelope addressed to: Commissioner for Patents, Serial No.: 10/684,936 P.O. Box 1450, Alexandria, VA 22313-1450 on Filed: October 14, 2003 (Date of Deposit) Shannon Wallace Semiconductor Device And Method) For: Name of applicant, assignee, or Registered Rep. Of Fabricating The Same Signature Date Examiner: Thien F. Tran

Commissioner for Patents P.O. Box 1450 Alexandria, VA 23313-1450

2811

Art Unit:

RESPONSE B (AFTER FINAL)

Applicants have the following response to the Final Rejection of April 5, 2005, a one month extension of time being submitted herewith. Applicants will address each of the Examiner's rejections in the order in which they appear in the Final Rejection.

Claim Rejections - 35 USC §112

In the Final Rejection, the Examiner rejects Claims 81-85 under 35 USC §112, first paragraph, as failing to comply with the written description requirement. This rejection is respectfully traversed.

In particular, the Examiner contends that the "recitation of an electrode through the first silicon nitride oxide film and the second silicon nitride oxide film sets forth a structure not supported